



HIGH FREQUENCY HIGH-SIDE AND LOW-SIDE GATE DRIVER IN W-DFN3030-10 (Type TH)

Description

The DGD0507A is a high-frequency gate driver capable of driving N-channel MOSFETs. The floating high-side driver is rated up to 50V.

The DGD0507A logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with MCUs. UVLO for high-side and low-side will protect a MOSFET with loss of supply. To protect MOSFETs, cross conduction prevention logic prevents the HO and LO outputs from being on at the same time.

Fast and well-matched propagation delays allow a higher switching frequency, enabling a smaller, more compact power switching design, using smaller associated components. To minimize space an internal bootstrap diode is included. The DGD0507A is offered in the W-DFN3030-10 (Type TH) package and operates over an extended - 40°C to +125°C temperature range.

Applications

- DC-DC Converters
- Motor Controls
- Battery Powered Hand Tools
- eCig Devices
- Class D Power Amplifiers

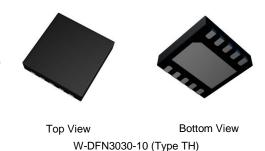
V_{CC} V_B HIN DGD0507A LIN DGD0507A V_S EN LO COM Typical Configuration

Features

- 50V Floating High-side Driver
- Drives Two N-channel MOSFETs in a Half-bridge Configuration
- 1.5A Source / 2.0A Sink Output Current Capability
- Internal Bootstrap Diode Included
- Undervoltage Lockout for High-Side and Low-Side Drivers
- Delay Matching a Typical of 5ns
- Propagation Delay Typical of 20ns
- Logic Input (HIN, LIN and EN) 3.3V Capability
- Ultra Low Standby Currents (<1µA)
- Extended Temperature Range: -40°C to +125°C
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: W-DFN3030-10 (Type TH)
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Weight: 0.017 grams (Approximate)



Ordering Information (Note 4)

Product	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DGD0507AFN-7	DGD0507A	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

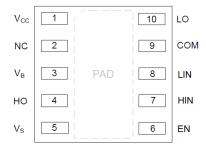
Marking Information



DGD0507A = Product Type Marking Code YY = Year (ex: 18 = 2018) WW = Week (01 to 53)



Pin Assignments

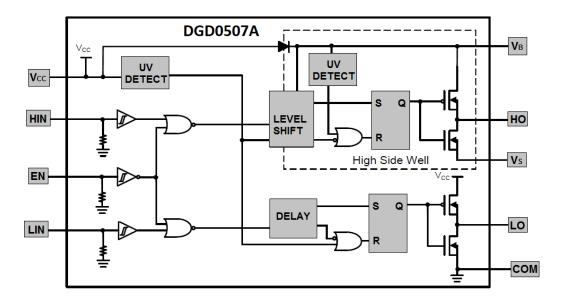


Top View: W-DFN3030-10 (Type TH)

Pin Descriptions

Pin Number	Pin Name	Function
1	Vcc	Low-Side and Logic Supply
2	NC	No connect (No Internal Connection)
3	V _B	High-Side Floating Supply
4	НО	High-Side Gate Drive Output
5	Vs	High-Side Floating Supply Return
6	EN	Logic Input Enable, a Logic Low turns off Gate Driver
7	HIN	Logic Input for High-Side Gate Driver, in Phase with HO
8	LIN	Logic Input for Low-Side Gate Driver, in Phase with LO
9	COM	Low-Side and Logic Return
10	LO	Low-Side Gate Drive Output
PAD	Substrate	Connect to COM on PCB

Functional Block Diagram





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
High-Side Floating Positive Supply Voltage	V _B	-0.3 to +60	V
High-Side Floating Negative Supply Voltage	Vs	V _B -14 to V _B +0.3	V
High-Side Floating Output Voltage	V _{HO}	V _S -0.3 to V _B +0.3	V
Offset Supply Voltage Transient	dV _S / dt	50	V/ns
Logic and Low-Side Fixed Supply Voltage	Vcc	-0.3 to +14	V
Low-Side Output Voltage	V _{LO}	-0.3 to V _{CC} +0.3	V
Logic Input Voltage (HIN, LIN and EN)	V _{IN}	-0.3 to V _{CC} +0.3	V

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor (Note 5)	P _D	0.4	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	64	°C/W
Thermal Resistance, Junction to Case (Note 5)	R _{eJC}	42	°C/W
Operating Temperature	TJ	+150	
Lead Temperature (Soldering, 10s)	TL	+300	°C
Storage Temperature Range	T _{STG}	-55 to +150	

Note:

5. When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
High-Side Floating Supply	V _B	V _S + 8	V _S + 14	V
High-Side Floating Supply Offset Voltage	Vs	(Note 6)	50 (Note 7)	V
High-Side Floating Output Voltage	V_{HO}	V_S	V_{B}	V
Logic and Low Side Fixed Supply Voltage	V _{CC}	8	14	V
Low-Side Output Voltage	V_{LO}	0	V_{cc}	V
Logic Input Voltage (HIN, LIN and EN)	V _{IN}	0	5	V
Ambient Temperature	T _A	-40	+125	°C

Notes:

^{6.} Logic operation for V_S of -5V to +50V.

^{7.} Provided V_B doesn't exceed absolute maximum rating of 60V.

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$\textbf{DC Electrical Characteristics} \ (V_{CC} = V_{BS} = 12 \text{V}, \ \text{COM} = V_{S} = 0 \text{V}, \ @T_{A} = +25 ^{\circ}\text{C}, \ \text{unless otherwise specified.}) \ (\text{Note 8})$

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Logic "1" Input Voltage	V _{IH}	2.4	-	ı	V	_
Logic "0" Input Voltage	V _{IL}	-	_	0.8	V	_
Enable Logic "1" Input Voltage	V _{ENIH}	1.5	_	-	V	_
Enable Logic "0" Input Voltage	V _{ENIL}	_	_	0.7	V	_
Input Voltage Hysteresis	VINHYS	-	0.6	-	V	_
Enable Input Voltage Hysteresis	V _{ENINHYS}	_	0.1	-	V	_
High Level Output Voltage, VBIAS - VO	VoH	_	0.45	0.6	V	$I_{O+} = 100 \text{mA}$
Low Level Output Voltage, VO	V_{OL}	_	0.15	0.22	V	$I_{O-} = 100 \text{mA}$
Offset Supply Leakage Current	I _{LK}	-	1	5	μΑ	$V_B = V_S = 60V$
V _{CC} Shutdown Supply Current	I _{CCSD}	_	0	1	μΑ	$V_{IN} = 0V$ or 5V, $V_{EN} = 0V$
V _{CC} Quiescent Supply Current	Iccq	_	130	200	μΑ	$V_{IN} = 0V \text{ or } 5V$
V _{CC} Operating Supply Current	ICCOP	-	7.3	-	mA	$fs = 500kHz, C_L = 1000pF$
V _{BS} Quiescent Supply Current	I _{BSQ}	_	40	100	μΑ	V _{IN} = 0V or 5V
V _{BS} Operating Supply Current	I _{BSOP}	_	7.3	-	mA	$fs = 500kHz, C_L = 1000pF$
Logic "1" Input Bias Current	I _{IN+}	-	_	50	μΑ	$V_{IN} = 5V$
Logic "0" Input Bias Current	I _{IN-}	-	_	5	μΑ	$V_{IN} = 0V$
Enable Logic "1" Input Bias Current	I _{ENIN+}	_	43	60	μΑ	$V_{IN} = 5V$
Enable Logic "0" Input Bias Current	I _{ENIN} -	_	0	5	μΑ	$V_{IN} = 0V$
V _{BS} Supply Undervoltage Positive Going Threshold	V _{BSUV+}	6.0	7.0	8.0	V	_
V _{BS} Supply Undervoltage Negative Going Threshold	V _{BSUV} -	5.6	6.6	7.6	V	_
V _{CC} Supply Undervoltage Positive Going Threshold	V _{CCUV+}	6.0	7.0	8.0	V	_
V _{CC} Supply Undervoltage Negative Going Threshold	V _{CCUV} -	5.6	6.6	7.6	V	_
Output High Short Circuit Pulsed Current	I _{O+}	0.9	1.5	-	Α	V _O = 0V, PW ≤ 10μs
Output Low Short Circuit Pulsed Current	I _O -	1.5	2.0	-	Α	V _O = 15V, PW ≤ 10µs
Forward Voltage of Bootstrap Diode	V _{F1}	-	0.67	-	V	I _F = 100μA
Forward Voltage of Bootstrap Diode	V_{F2}	-	1.7	_	V	I _F = 100mA

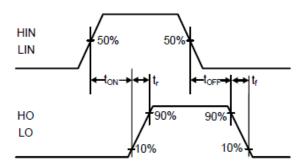
Note: 8. The V_{IN} and I_{IN} parameters are applicable to the two logic pins: HIN, LIN and EN. The V_O and I_O parameters are applicable to the respective output pins: HO and LO.

AC Electrical Characteristics ($V_{CC} = V_{BS} = 12V$, COM = $V_S = 0V$, $C_L = 1000 pF$, @ $T_A = +25 ^{\circ}C$, unless otherwise specified.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Turn-on Propagation Delay	t _{ON}	_	20	35	ns	_
Turn-off Propagation Delay	t _{OFF}	_	23	56	ns	$V_S = 50V$
Delay Matching, HO & LO Turn-on	t _{DM}	_	_	5	ns	_
Turn-on Rise Time	t _R	_	16	30	ns	-
Turn-off Fall Time	t _F	_	18	25	ns	_



Timing Waveforms



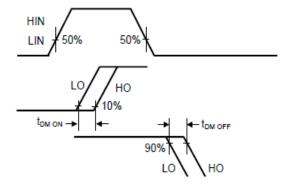


Figure 1. Switching Time Waveform Definitions

Figure 2. Delay Matching Waveform Definitions

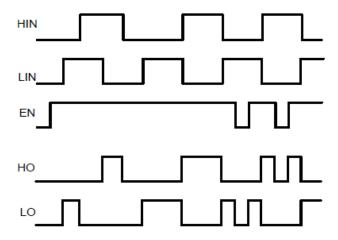


Figure 3. Input / Output Timing Diagram



Typical Performance Characteristics (@T_A = +25°C, unless otherwise specified.)

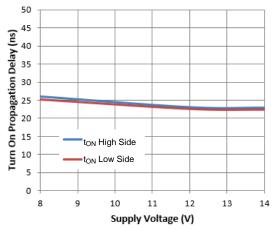


Figure 4. Turn-on Propagation Delay vs. Supply Voltage

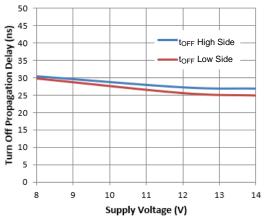


Figure 6. Turn-off Propagation Delay vs. Supply Voltage

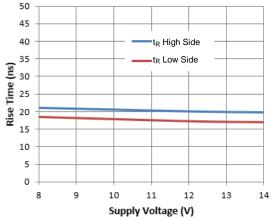


Figure 8. Rise Time vs. Supply Voltage

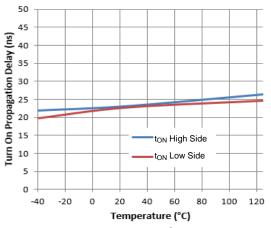


Figure 5. Turn-on Propagation Delay vs. Temperature

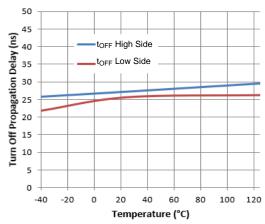


Figure 7. Turn-off Propagation Delay vs. Temperature

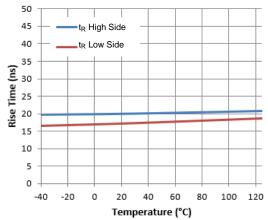


Figure 9. Rise Time vs. Temperature



Typical Performance Characteristics (Cont.)

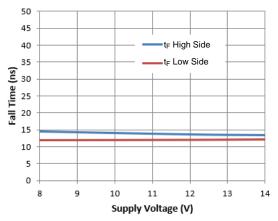


Figure 10. Fall Time vs. Supply Voltage

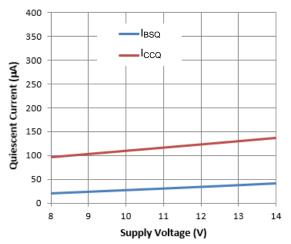


Figure 12. Quiescent Current vs. Supply Voltage

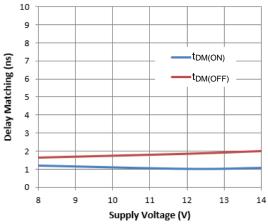


Figure 14. Delay Matching vs. Supply Voltage

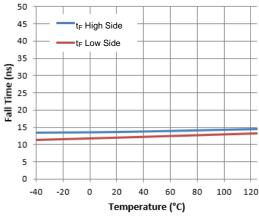


Figure 11. Fall Time vs. Temperature

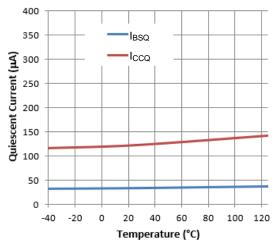


Figure 13. Quiescent Current vs. Temperature

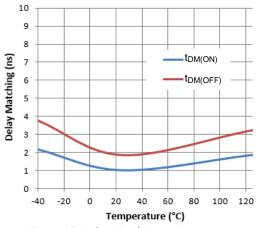


Figure 15. Delay Matching vs. Temperature



Typical Performance Characteristics (Cont.)

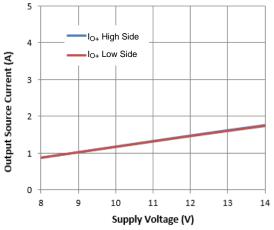


Figure 16. Output Source Current vs. Supply Voltage

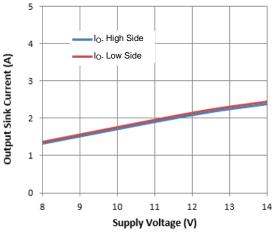


Figure 18. Output Sink Current vs. Supply Voltage

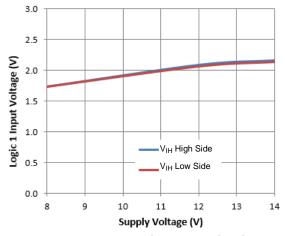


Figure 20. Logic 1 Input Voltage vs. Supply Voltage

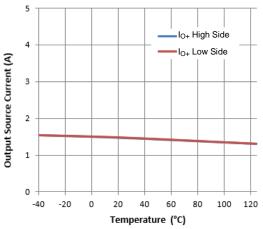


Figure 17. Output Source Current vs. Temperature

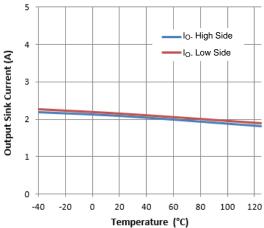


Figure 19. Output Sink Current vs. Temperature

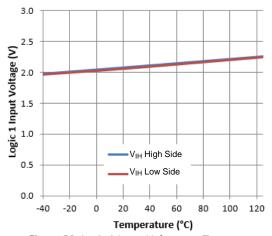


Figure 21. Logic 1 Input Voltage vs. Temperature



Typical Performance Characteristics (Cont.)

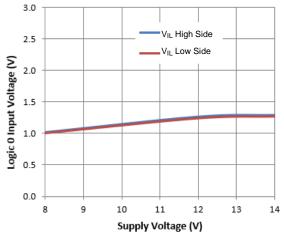


Figure 22. Logic 0 Input Voltage vs. Supply Voltage

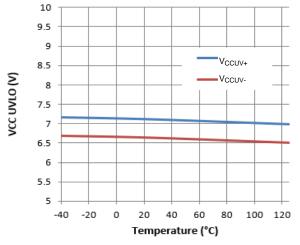


Figure 24. VCC UVLO vs. Temperature

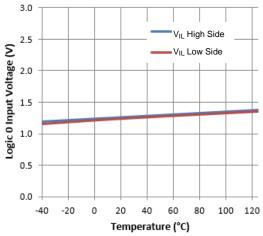


Figure 23. Logic 0 Input Voltage vs. Temperature

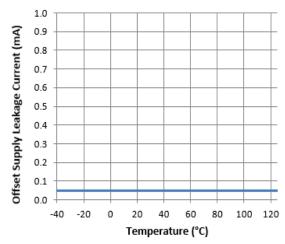


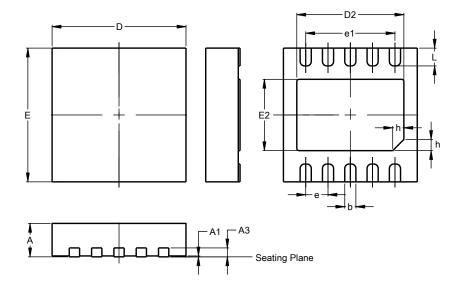
Figure 25. Offset Supply Leakage Current vs. Temperature



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

W-DFN3030-10 (Type TH)

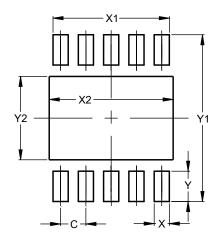


W-DFN3030-10							
	(Type TH)						
Dim	Min Max Typ						
Α	0.70	0.80	0.75				
A1	-	0.05	0.02				
A3	0.18	0.25	0.20				
b	0.18	0.30	0.25				
ם	2.90	3.10	3.00				
D2	2.40	2.60	2.50				
е		0.50BS	SC Si				
e1		2.00BS	SC Si				
Е	2.90	3.10	3.00				
E2	1.45	1.65	1.55				
h	0.20	0.30	0.25				
L	0.30	0.50	0.40				
All Dimensions in mm							

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

W-DFN3030-10 (Type TH)



Dimensions	Value (in mm)		
С	0.500		
X	0.300		
X1	2.300		
X2	2.600		
Y	0.600		
Y1	3.300		
Y2	1.650		



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